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81754.0048

F-485

FORM PTO-1083

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Art Unit:	2814 Phat X. Ca	o				
In re application of: Examiner:			this com	espon	dence	
Toshiniko HIGUCHI			INDRIBUSS	икиле и	J (1 4 4)	
Serial No: 09/754,818	872-9319 Washingt	Commis	sioner io	Larei	1125.	
Filed: January 4, 2001 For: SEMICONDUCTOR DEVICE HAVING A WIRING FOR: MANUFACTURING	wasningt	on D.C. 2 4. 2003	0201, 0			
FOR: SEMICONDUCTOR DEVICE FRANKS PATTERN AND METHOD FOR MANUFACTURING	Date 0	March 14, 2003 Date of Deposit				
THE SAME	Diane Z					
	Mame	24)	03/	/14/03	
	Signatu	* 21	سمم		Date	
Box AF				- T	77- 5	
Commissioner for Patents		FAX	REC	ノニ!	VED	
Washington, D.C. 20231						
Dear Sir:		M	AR 1	4 20	103	
Dear Sir: Transmitted herewith is an Amendment in the above-identified application. Transmitted herewith is an Amendment in the above-identified application.						
Transmitted herewith is an Amendment of the See 37 CFR § 1.27. Small entity status has been claimed. See 37 CFR § 1.27.	7	ECHNO	LOGY	CENT	ER 28	
-						
No additional fee is required.						
The fee has been calculated as shown below: (Col. 2)	10-1-2)		******			
(COL-1)) DICUCST NUMBER]	(Col. 3) PRESENT	LG/SM S ENTITY FEE			DUE	
CLAIMS REMAINING HIGHEST NUMBER AFTER AMENDMENT PREVIOUSLY PAID FOR	EXTRA*		1	-		
20	0	LG=\$18 SM=\$9	\$18.00	\$		
TOTAL CLAIMS FEE 20		LG=\$84		\$	0	
INDEPENDENT 7 - 8		SM=\$42 ENTITY FE		5		
CLAIMS FEI! FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIMS	SMALL	ENTITY FE	E - \$140			
			TOTAL	\$	٥	
Independent Claims: 1, 7, 8, 9, 10, 11, 12						
 If the entry in Col. 1 is less than the entry in Col. 2, write "0" In Col. 3. If the entry in Col. 1 is less than the entry in Col. 2, write "0" In Col. 3. If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, write "3" in this space. If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, write "3" in this space. 	pace.	umber Pre	dously Pai	id For	(Total or	
* If the Highest Number Provider Park Por IN THIS SPACE is less than 3, write a monday	ent or the number o	f claims ori	ginally file	d.		
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Any patent application processing tools Respectfully s						
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Date: March 14, 2003

Biltmore Tower 500 South Grand Avenue, Suite 1900

Telephone: (213) 337-6700 Facsimile: (213) 337-6701

Erin P. Madill

Registration No. 46,893 Attorneys for Applicant

03:25pm

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500 SOUTH GRAND AVENUE SUITE 1900 LOS ANGELES, CA 90071

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IMPORTANT NOTICE TELECOPY/FACSIMILE COVER LETTER

WASHINGTON, DC BRUSSELS BUDAPEST* LONDON MOSCOW PÀRIS* PRAGUE* TOKYO WARSAW BALTIMORE, MD BOULDER, CO COLORADO SPRINGS, CO DENVER, CO IRVINE, CA McLEAN, VA MIAMI, FL NEW YORK, NY (PARK AVE) NEW YORK, NY (THIRD AVE)
ROCKVILLE, MD

*Affiliated Office

•	ro: _	U.S. Patent and Trad	emark Office		DATE:	March 14, 2003
	_	Examiner: Pha Art Unit: 2	2814			
	FROM:	Erin P. Ma	dill		TIME:	
		L NO. OF PAGES, INCLUDING COVER:				
	message is no please note t communicati	information is CONFIDENT of the intended recipient(s) of hat any dissemination, distri on in error should notify us i				
L	U.S. Mail.					
	SACE: Patent App hereby cel	olication No.: 09/754,81	8; Our Ref. 81754. locuments:	0048.	FAX R	ECEIVED
	•				MAR	1 4 2003
Ø	Amendm	ent Transmittal ent Under 37 C.F.R. § 1			TECHNOLO	GY CENTER 2800
ar	e being fac	similed to the Commiss	ioner for Patents, Wa	ishington, D.C. 2	U23 L.	
		March 14, 2003 Date of Deposit	Liene	Symu Diane Zynn	_ -	
	TELI	ECOPY/FAX NUMBER:	703-87	2-9319 ART UNI	T 2814	
		CLIENT NUMBER:	81754.	0048		
	ATTORN	EY BILLING NUMBER:	3606			
		FIRMATION NUMBER:	703-30	8-4917 (return fax 1	to Diane Zynn)	

PATENT 81754.0048

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Toshihiko HIGUCHI

Serial No: 09/754,818

Filed: January 4, 2001

For: SEMICONDUCTOR DEVICE HAVING A

WIRING PATTERN AND METHOD FOR

MANUFACTURING THE SAME

AMENDMENT UNDER 37 C.F.R. § 1.116

Box AF Commissioner for Patents Washington, D.C. 20231

Dear Sir:

Art Unit:

2814

Examiner: Phat X. Cao

Signature

I hereby certify that this correspondence is being transmitted via facsimile to (703) 872-9319: Commissioner for Patents, Washington D.C. 20231, on

March 14, 2003

Date of Deposit

Diane Zynn

TName

03/14/03 Date

M.Brumon 5 21 03

In response to the Final Office Action dated December 17, 2002, please amend the above-referenced application as follows:

FAX RECEIVED

IN THE CLAIMS:

Please replace the text of claim 1 with the following text:

MAR 1 4 2003

TECHNOLOGY CENTER 2800

(Amended) A semiconductor device having a wiring pattern that is
formed by etching a conductive layer using a resist pattern as a mask, the semiconductor
device comprising:

a contact section formed in an interlayer dielectric layer;

a first wiring formed over the interlayer dielectric layer and disposed with a separation from the contact section shorter than a specified separation; and

a second wiring having a connection region connected to the contact section,

wherein the second wiring has an extension section extending in a non-wiring region in the connection region connected to the contact section, and

the extension section extends from at least one section of the connection region other than sides of the connections region facing the first wiring.

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